Product data sheet

1. Product profile

1.1 General description

Planar passivated sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring enhanced noise immunity and direct interfacing to logic ICs and low power gate drivers.

1.2 Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Triggering in all four quadrants

1.3 Applications

- General purpose low power motor control
- Home appliances

- Industrial process control
- Low power AC Fan controllers

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see Figure 4; see Figure 5	-	-	12.5	Α
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 45 °C; see <u>Figure 1</u> ; see <u>Figure 3</u> ; see <u>Figure 2</u>	-	-	1	Α



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{ Company of the company$	0.4	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{ Company of the company $	0.4	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ Composition}}$	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	0.4	-	10	mA

2. Pinning information

Table 2. Pinning information

	•	•		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2	-	. .
2	G	gate		T2T1
3	T1 main terminal 1		`G sym051	
			SOT54 (TO-92)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
Z0109NA0	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 45 °C; see <u>Figure 1</u> ; see <u>Figure 3</u> ; see <u>Figure 2</u>	-	1	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 ms$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	12.5	Α
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms	-	13.8	Α
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	0.78	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2+ G+	-	50	A/µs
		$I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$; $T2+$ $G-$	-	50	A/µs
		$I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$; T2- G-	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	Α
P_{GM}	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

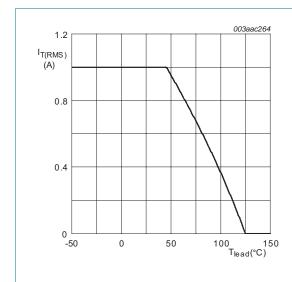
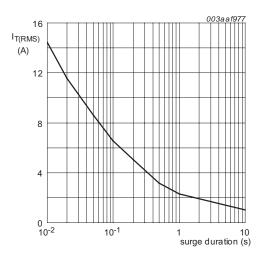


Fig 1. RMS on-state current as a function of lead temperature; maximum values



f = 50Hz, $T_{lead} = 45$ °C

Fig 2. RMS on-state current as a function of surge duration; maximum values

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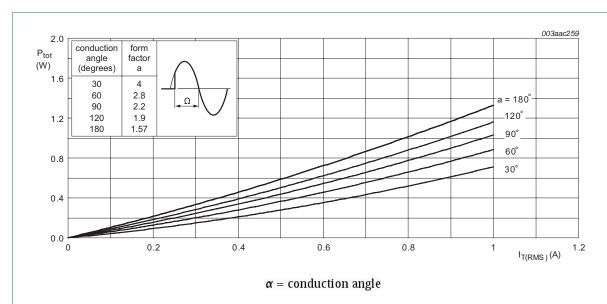


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

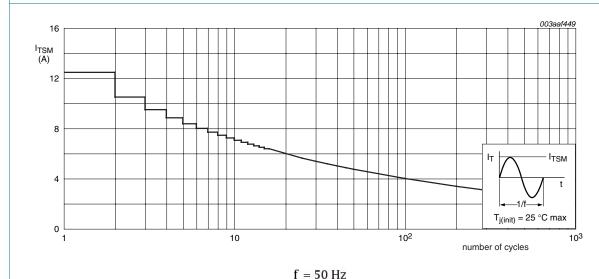
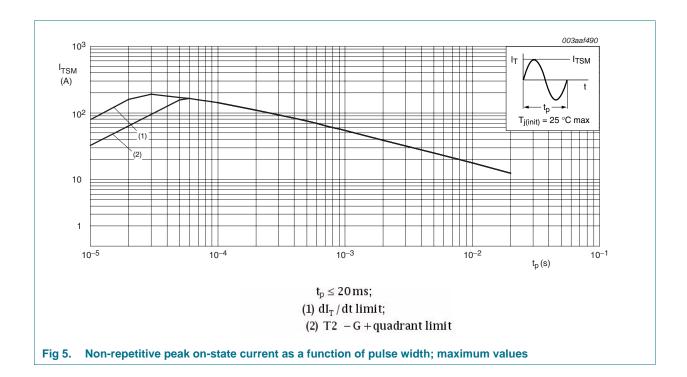


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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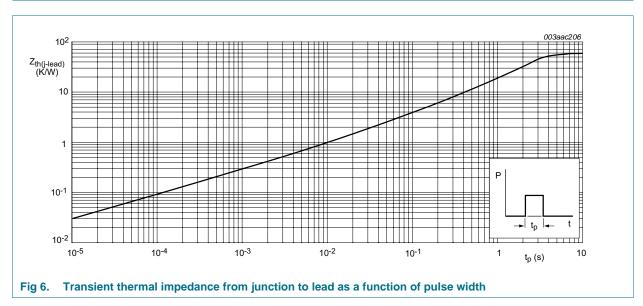


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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; see Figure 6	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	full cycle; printed-circuit board mounted; lead length 4 mm	-	150	-	K/W



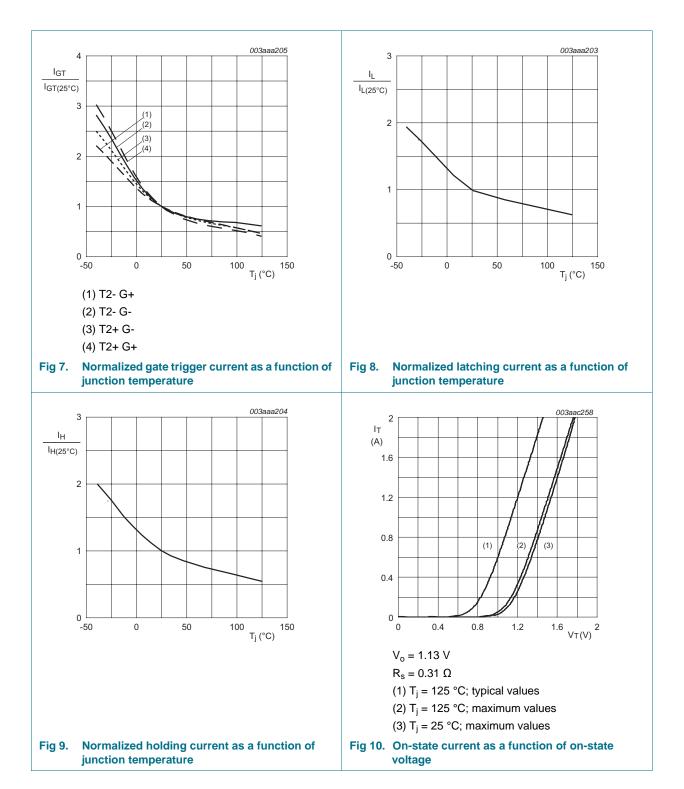
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6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+; T_j = 25 \text{ °C;}$ see Figure 7	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 °C;$ see Figure 7	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G-; T_j = 25 ^{\circ}\text{C};$ see Figure 7	0.4	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+; T_j = 25 °C;$ see Figure 7	0.4	-	10	mA
IL I	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+G+; T_j = 25 \text{ °C;}$ see Figure 8	-	-	15	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ \text{ G-; } T_j = 25 \text{ °C; }$ see Figure 8	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+; T_j = 25 °C;$ see Figure 8	-	-	15	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$	-	-	10	mΑ
V _T	on-state voltage	I _T = 1 A; T _j = 25 °C; see <u>Figure 10</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11	-	-	1.3	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.2	-	-	V
I _D	off-state current	$V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	-	0.5	mΑ
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; gate open circuit; exponential waveform; see Figure 12	120	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 \text{ °C};$ $dl_{com}/dt = 0.44 \text{ A/ms};$ gate open circuit	2	-	-	V/µs





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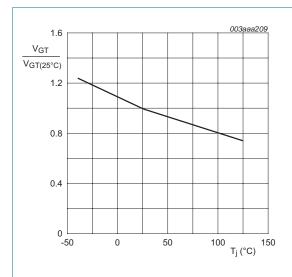


Fig 11. Normalized gate trigger voltage as a function of junction temperature

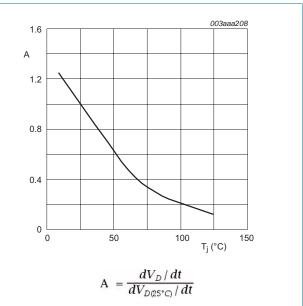


Fig 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

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7. Package outline

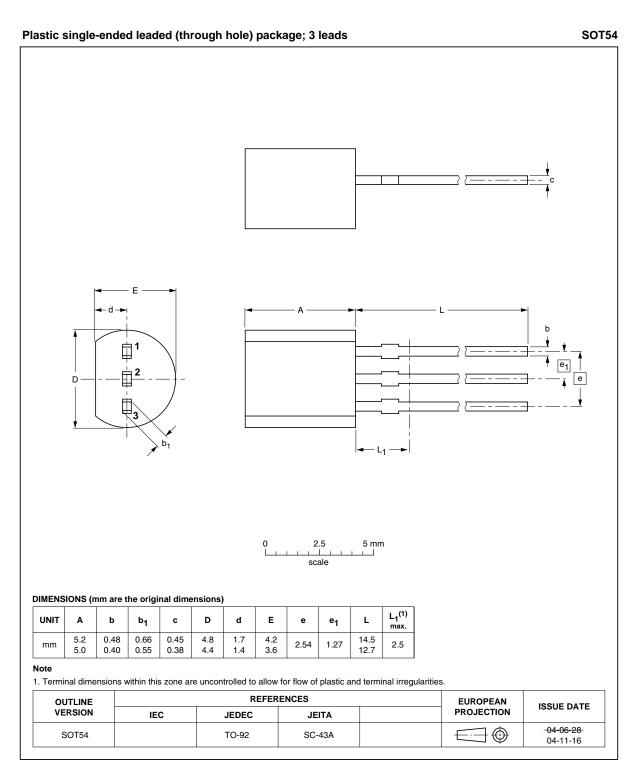
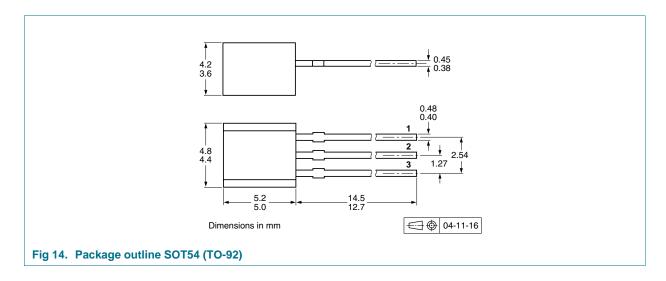


Fig 13. Package outline SOT54 (TO-92)

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8. Package outline



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9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Z0109NA0 v.3	20110512	Product data sheet	-	Z0109NA0 v.2
Modifications:	 Various chang 	jes to content.		
Z0109NA0 v.2	20110318	Product data sheet	-	Z0109NA0 v.1

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10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Date of release: 12 May 2011 Document identifier: Z0109NA0